

WHAT IS CLAIMED IS:

1. An electroluminescent device comprising:  
first electrodes;  
electroluminescent layers disposed over the first electrodes;  
a second electrode disposed to over the electroluminescent layers; and  
a barrier layer in direct contact with the second electrode,  
wherein at least the surface of the second electrode facing the barrier layer  
comprises an inorganic oxide, and  
at least the surface of the barrier layer facing the second electrode comprises  
an inorganic compound.
2. The electroluminescent device according to claim 1,  
wherein the second electrode comprises indium tin oxide or indium zinc oxide.
3. The electroluminescent device according to claim 1,  
wherein the second electrode covers side faces and upper faces of the  
electroluminescent layers.
4. The electroluminescent device according to claim 1,  
wherein the barrier layer comprises at least one sublayer composed of a silicon  
compound.
5. The electroluminescent device according to claim 4,  
wherein the barrier layer comprises a sublayer in contact with the second  
electrode, the sublayer being composed of silicon oxide.
6. The electroluminescent device according to claim 4,  
wherein the barrier layer comprises a sublayer in contact with the second  
electrode, the sublayer being composed of silicon nitride.
7. The electroluminescent device according to claim 4,  
wherein the barrier layer comprises a sublayer in contact with the second  
electrode, the sublayer being composed of silicon nitride oxide.
8. The electroluminescent device according to claim 1, further comprising:  
an insulating layer disposed around the second electrode, the insulating layer  
being composed of a silicon compound,  
wherein the barrier layer extends to the insulating layer.
9. The electroluminescent device according to claim 1, further comprising:  
a protective layer for covering the barrier layer.
10. The electroluminescent device according to claim 9, further comprising:

an adhesive layer disposed between the barrier layer and the protective layer.

11. The electroluminescent device according to claim 10,  
wherein the adhesive layer comprises a material softer than that of the protective layer.
12. An electronic apparatus comprising an electroluminescent device according to claim 1.
13. A method for manufacturing an electroluminescent device, comprising the steps of:  
forming a second electrode to over electroluminescent layers disposed over a first electrode, the second electrode having a surface being composed of an inorganic oxide;  
and  
forming a barrier layer such that at least one portion of the barrier layer comes into direct contact with the second electrode, the barrier layer being composed of an inorganic compound.
14. The method for manufacturing an electroluminescent device according to claim 13,  
wherein the second electrode is formed by vapor phase deposition.
15. The method for manufacturing an electroluminescent device according to claim 13,  
wherein the barrier layer is formed by vapor phase deposition.
16. The method for manufacturing an electroluminescent device according to any one of claim 13,  
wherein the second electrode comprises indium tin oxide or indium zinc oxide.
17. The method for manufacturing an electroluminescent device according to any one of claim 13,  
wherein the barrier layer comprises a silicon compound.
18. The method for manufacturing an electroluminescent device according to claim 17,  
wherein the barrier layer has a sublayer in contact with the second electrode, the sublayer being composed of silicon oxide.
19. The method for manufacturing an electroluminescent device according to claim 17,  
wherein the barrier layer has a sublayer in contact with the second electrode, the sublayer being composed of silicon nitride.

20. The method for manufacturing an electroluminescent device according to claim 17,

wherein the barrier layer has a sublayer in contact with the second electrode, the sublayer being composed of silicon nitride oxide.

21. The method for manufacturing an electroluminescent device according to claim 13,

wherein the barrier layer extends to an insulating layer disposed around the second electrode, the insulating layer being composed of a silicon compound.